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Supplementary information

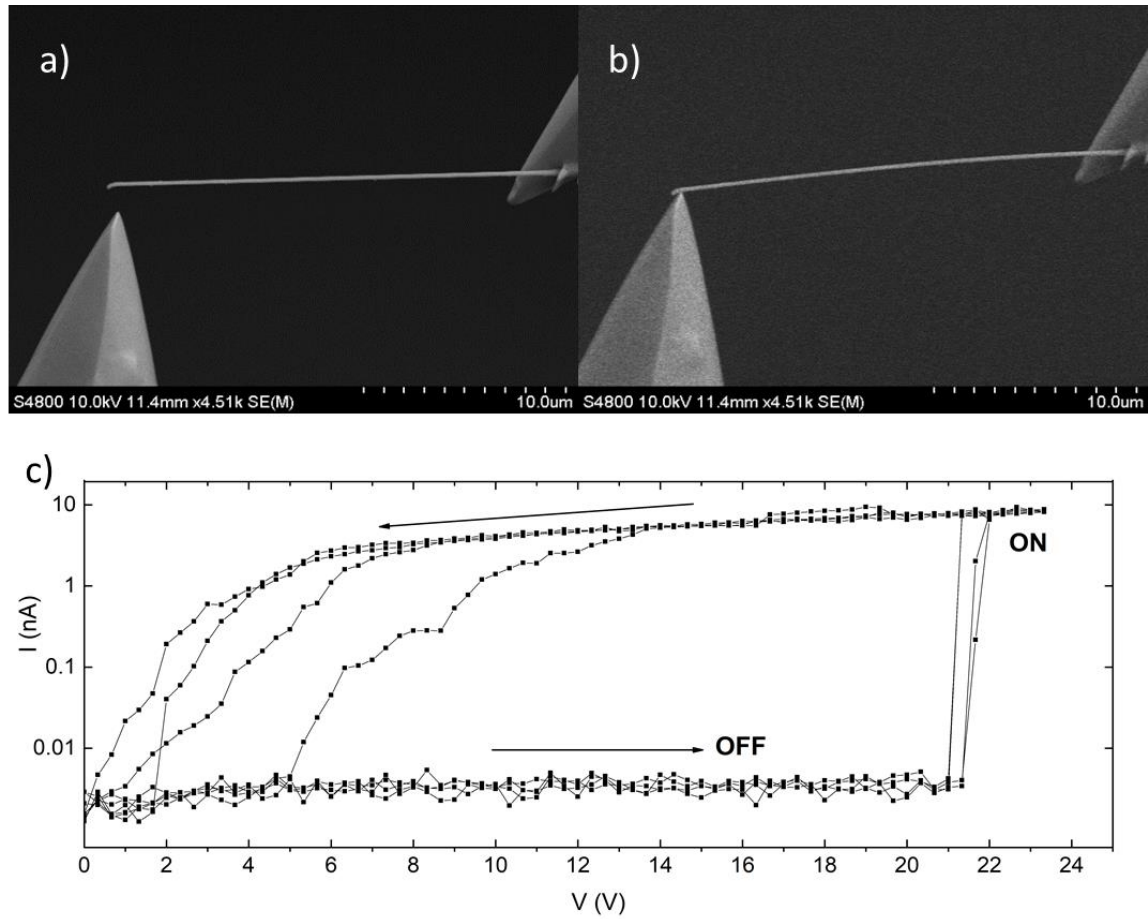


Figure 1. Additional NEM device with repeated measurements for GeSn nanowire with $L = 22 \mu\text{m}$, $d = 125 \text{ nm}$. a) – nanowire in an OFF state; b) – nanowire in ON state, c) – repeated IV measurements of NEM device. The AC assisted jump in occurred at $5 \text{ V} + 0.6 \text{ V DC} + \text{AC}$ voltage.